Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low forward voltage drop
- · Low thermal resistance
- · Soft recovery characteristic

3. Applications

- · High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	80	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	88	A
Static charac	cteristics					
V_{F}	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
Dynamic cha	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	35	50	ns

Ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	Α	anode		001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV10-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

2/10

Ultrafast power diode

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; $T_{mb} \le 109$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \le 109$ °C; square-wave pulse	-	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	80	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	88	Α
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

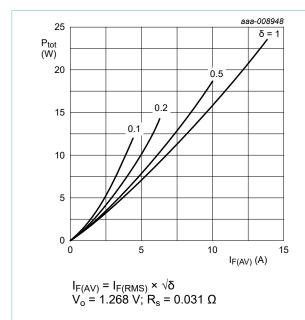


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

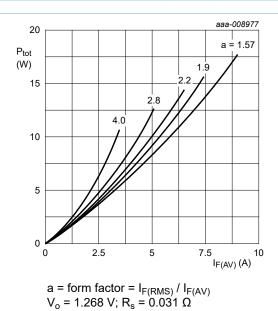


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

3 / 10

Ultrafast power diode

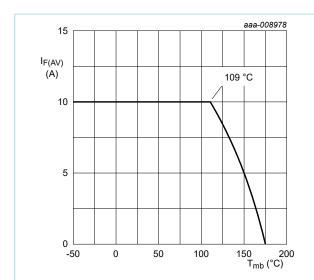


Fig. 3. Forward current as a function of mounting base temperature; maximum values

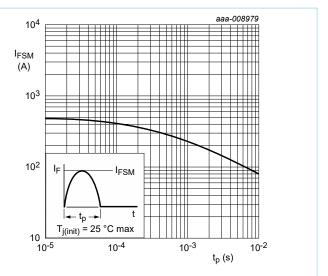


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

4 / 10

Ultrafast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	3.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

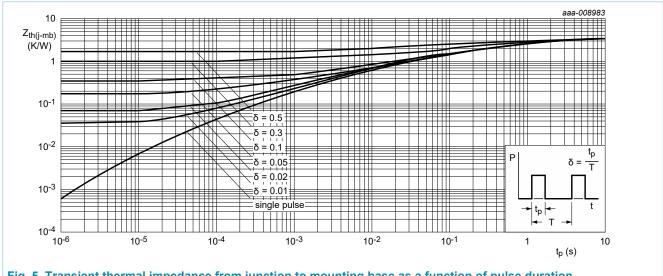


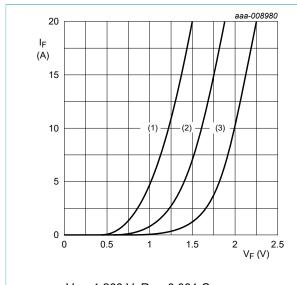
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

Ultrafast power diode

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 500 V; T _j = 150 °C	-	-	250	μΑ
Dynamic cl	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	35	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	20	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	40	-	ns



 V_o = 1.268 V; R_s = 0.031 Ω (1) T_j = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values



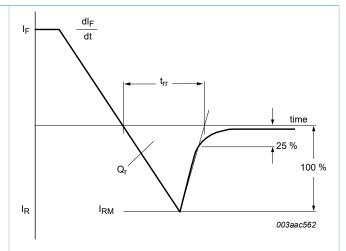
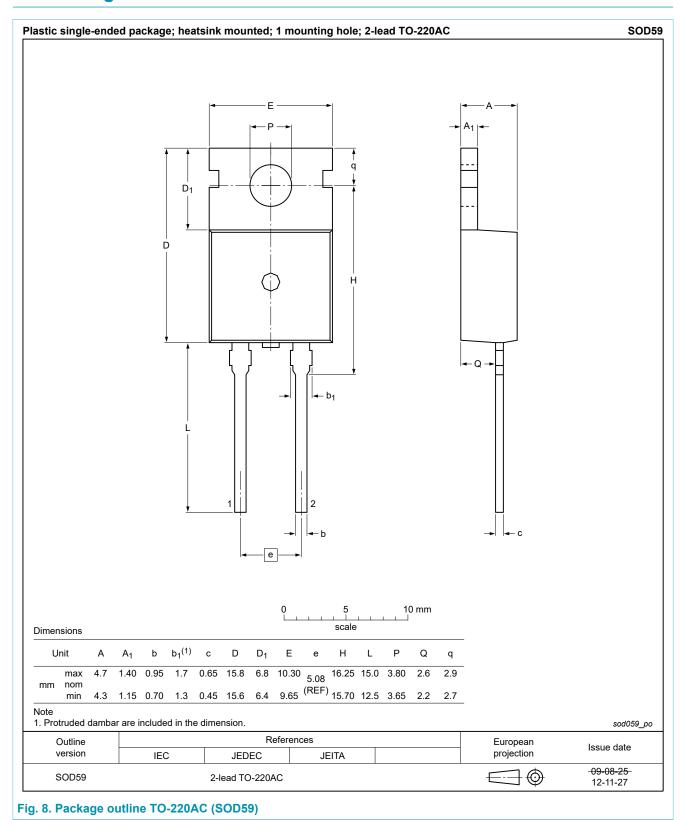


Fig. 7. Reverse recovery definitions; ramp recovery

Ultrafast power diode

10. Package outline



Ultrafast power diode

11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Ultrafast power diode

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Ultrafast power diode

12. Contents

1.	General description	1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	. 3
8.	Thermal characteristics	. 5
9.	Characteristics	6
10.	Package outline	. 7
11.	Legal information	. 8

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Date of release: 26 September 2018

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